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Substitute for form 1449A/PTO				Complete if known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/638,406
				Filing Date	August 12, 2003
				First Named Inventor	Koji Sakui et al.
				Group Art Unit	2818
				Examiner Name	Unknown
Sheet	1	of	1	Attorney Docket Number	01701.00236

U.S. PATENT DOCUMENTS						
Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number ²	Kind Code ² (if known)			
ap		5515327		Matsukawa et al.	5-7-1996	
		5559735		Ono et al.	9-24-1996	
		5523980		Sakui et al.	6-4-1996	
		5615163		Sakui et al.	3-25-1997	
ap		4996669		Endoh et al.	2-26-1991	

FOREIGN PATENT DOCUMENTS								
Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₀
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
ap		EP	0797212	A2	Toshiba	9-24-1997		x
ap		JP	10-177797	A	Toshiba	6-30-1998		abst

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
ap		Takeuchi, Ken, et al., "A Double-Level-V _{th} Select Gate Array Architecture for Multilevel NAND Flash Memories," IEICE Trans. Electron., Vol. E79-C, No. 7, July 1, 1996, pp. 1013-1020	
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Examiner Signature	<i>Anh Phung</i>	Date Considered	6/2/04
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet

1

of

2

Complete if Known

Application Number	TBA
Filing Date	Herewith
First Named Inventor	Koji Sakui et al.
Group Art Unit	Unknown
Examiner Name	Unknown.
Attorney Docket Number	01701.00236

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
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		Filing Date	Herewith
		First Named Inventor	Koji Sakui et al.
		Group Art Unit	Unknown
		Examiner Name	Unknown.
Sheet 2 of 2	Attorney Docket Number	01701.00236	

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
ap		"SESSION XII: ROMs, PROMs AND EROMs THPM 12.6:A 16Kb Electrically Erasable Nonvolatile Memory", William S. Johnson, et al. ISSCC 80/1980, IEEE International Solid-State Circuits Conference, CH 1490-2/80/0000/0152, pp. 152-153, Feb. 14, 1980	
ap		"A New Flash E ² Prom Cell Using Triple Polysilicon Technology", Fujio Masuoka, et al., 464-467 - IEDM 84, CH2099-0/84/0000-0464; 17.3 (1984)	
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ap		Atsushi Nozoe et al., ISSCC99/Session 6/Paper MP6.5, "A 256 Mb Multilevel Flash Memory with 2MB/s Program Rate for Mass Storage Applications," pp. 1-6	

Examiner Signature	<i>Anh Phung</i>	Date Considered	6/2/04
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